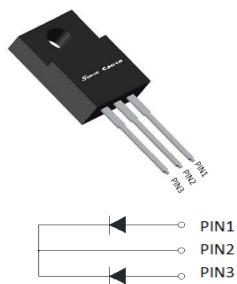


MBR20F60FCTS

Schottky Diodes



Features

- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

Typical Applications

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

Mechanical Data

• Package: ITO-220AB

Molding compound meets UL 94 V-0 flammability

• Terminals: Tin plated leads, solderable per J-STD-

002 and JESD22-B102 • Polarity: As marked

■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBR20F60FCTS
Device marking code			MBR20F60FCTS
Repetitive Peak Reverse Voltage	VRRM	V	60
Average Rectified Output Current @60Hz sine wave, R-load, Tc=90°C	lo	Α	20
Surge(Non-repetitive)Forward Current @60Hz half sine-wave,1 cycle, Ta=25°C	IFSM	Α	150
Current Squared Time @1ms≤t≤8.3ms Tj=25°C,	l²t	A²s	94
Storage Temperature	T _{stg}	°C	-55 ~ + 150
Junction Temperature	Tj	°C	-55 ~ + 150

■Electrical Characteristics (T_a=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST	MBR20F60FCTS
	01202	O.V.	CONDITIONS	
Maximum instantaneous forward voltage drop per diode	VFM	V	IFM=10.0A	0.75
Maximum DC reverse current at rated DC blocking voltage per diode	IRRM1	mA	VRM=VRRM T _a =25°C	0.2
	IRRM2		VRM=VRRM T _a =125°C	50

Note1:Pulse test:300uS pulse widh,1% duty cycle

Note2:Pulse test:pulse widh 40mS



MBR20F60FCTS

■Thermal Characteristics (T_a=25°C Unless otherwise specified)

PARAMETER		SYMBOL UNIT		MBR20F60FCTS	
Thermal Resistance	Between junction and case	R _{θJ-C}	°C/W	4.0	

■Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBR20F60FCTS	Approximate 1.6	50	1000	5000	Tube

■Characteristics (Typical)

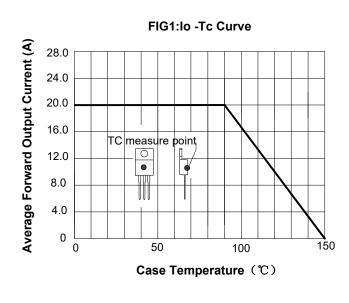
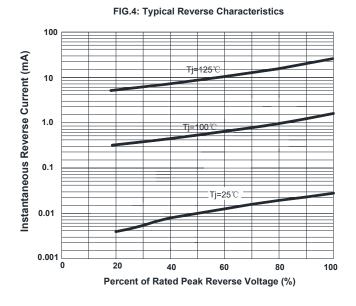


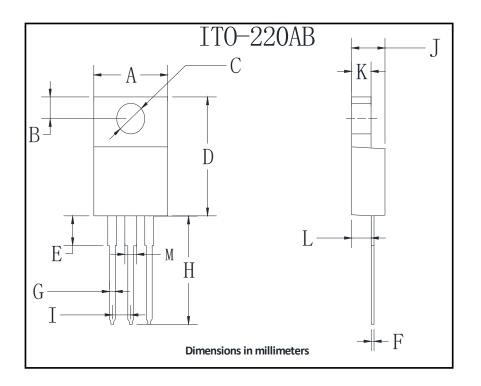
FIG2:Surge Forward Current Capability 175 Peak Forward Surge Current (A) 150 125 8.3ms Single Half Sine-Wave 100 JEDEC Method 75 50 25 2 20 50 100 **Number of Cycles**





MBR20F60FCTS

■Outline Dimensions



ITO-220AB				
Dim	Min	Max		
Α	9.8	10.2		
В	2.25	2.75		
С	2.95	3.45		
D	14.75	15.25		
Е	3.05	3.95		
F	0.45	0.75		
G	0.45	0.75		
Н	13.4	14.2		
I	2.35	2.75		
J	4.3	4.8		
K	2.58	2.82		
L	2.58	2.82		
М	1.47	1.77		

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